2025-02-14(금), 10:55-12:40
좌장: 추후업데이트 예정

K. Memory (Design & Process Technology) 분과

[FK2-K] Ferroelectric and Oxide Channel based Memory Technology

FK2-K-1 10:55-11:10	**Application-Dependent Bias Scheme Optimization for Ferroelectric-Tunnel-FET-Based One-Transistor Ternary Content-Addressable Memory** Minjeong Ryu, Jae Seung Woo, Yeonwoo Kim, and Woo Young Choi Department Electrical and Computer Engineering, Inter-university Semiconductor Research Center, Seoul National University
FK2-K-2 11:10-11:25	**Achieving Low-Voltage Operation of 1T-nC FRAM via Precise Engineering of Polarization Switching Kinetics in Hafnia Ferroelectrics** Sangho Lee, Giuk Kim, Chaeheon Kim, Yunseok Nam, Junghyeon Hwang, Hunbeom Shin, Seokjoong Shin, and Sanghun Jeon School of Electrical Engineering, KAIST
FK2-K-3 11:25-11:40	**The Opportunity Of Anti-Ferroelectrics In FeFET For The Emerging Non-Volatile Memory Applications** School of Electrical Engineering, KAIST
FK2-K-4 11:40-11:55	**Comparison of Bi-Layer and Tri-Layer Structures in ZrO_2/ZnO/HfO_2 Synaptic Devices for Improved Neuromorphic Performance** Dong-Min Kim[1], Yu-Bin Kim[1], Sung-Ho Kim[1], Chae-Min Yeom[1], Shivam Kumar Gautam[1], Hyuk-Min Kwon[2], Yong-Goo Kim[3], and Hi-Deok Lee[1] [1]Department of Electronics Engineering, Chungnam National University, [2]School of Electronic & Electrical Engineering, Hankyong National university, [3]Department of Green Semiconductor System, Korea Polytechnics
FK2-K-5 11:55-12:10	**Study of IGZO-based CTF Memory with State Updates in Array** Ria Choi[1], Eunpyo Park[2], Heerak Wi[1], Dae Kyu Lee[2], Min Jee Kim[2], and Joon Young Kwak[1] [1]Ewha Womans University, [2]KIST

FK2-K-6 12:10-12:25	**Electrically Erasable Oxide-Semiconductor-Channel Charge Trap Flash Memory with Unipolar Operation** Chanyeong Go[1], Seongmin Park[1], and Yoonyoung Chung[1,2,3] [1]Department of Electrical Engineering, POSTECH, [2]Department of Semiconductor Engineering, POSTECH, [3]Center for Semiconductor Technology, POSTECH
FK2-K-7 12:25-12:40	**TCAD Simulation of 6T1C IGZO-Based Synaptic Device** Taegyeong Oh and Sung-Min Hong School of Electrical Engineering and Computer Science, Gwangju Institute of Science and Technology